

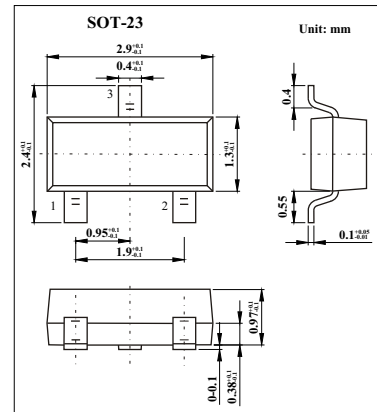
High Speed Switching Diode

1SS187

Features

Fast reverse recovery time: $t_{rr}=1.6\text{ns}(\text{typ.})$

Diode capacitance : $C_d=2.2\text{pF}(\text{typ.})$



Absolute Maximum Ratings $T_a = 25$

Parameter	Symbol	Rating	Unit
Maximum reverse voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Average forward current	I_O	100	mA
Maximum forward current	I_{FM}	300	mA
Surge current	I_{FSM}	2	A
Power dissipation	P_D	150	mW
Junction temperature	T_J	125	
Storage temperature range	T_{sig}	-55 to 125	

Electrical Characteristics $T_a = 25$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F=1\text{mA}$		0.61		V
		$I_F=10\text{mA}$		0.74		
		$I_F=100\text{mA}$		0.92	1.2	
Reverse voltage leakage current	I_R	$V_R=30\text{V}$			0.1	μA
		$V_R=80\text{V}$			0.5	
Diode capacitance	C_D	$V_R=0\text{V}, f=1\text{MHz}$		2.2	4	pF
Reverse recovery time	t_{rr}	$I_F=10\text{mA}$		1.6	4	ns

Marking

Marking	D3
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